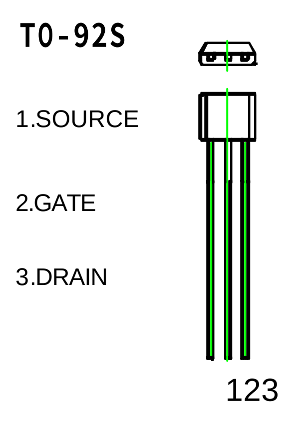
TO-92S Plastic-Encapsulate Transistors



K596 Si N-CHANNEL JUNCTION FET

FEATURES

Power dissipation

P_{CM}: 0.1W（Tamb=25℃）

Gate Current

I_G: 10mA

Drain current

I_D: 1mA

Drain-Source voltage

BV_{GDO}: -20 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

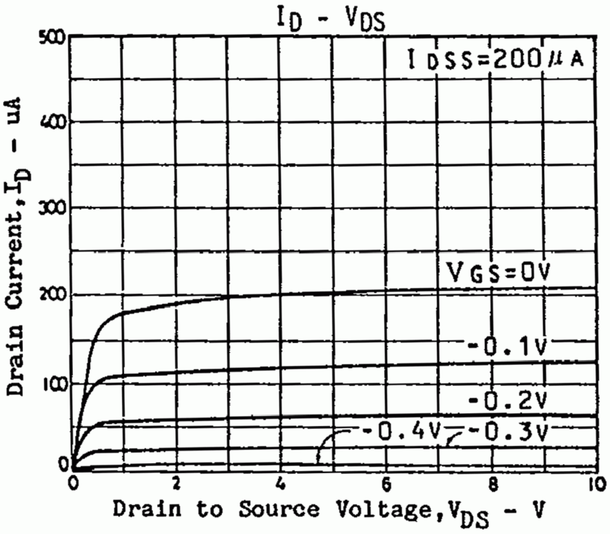
ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

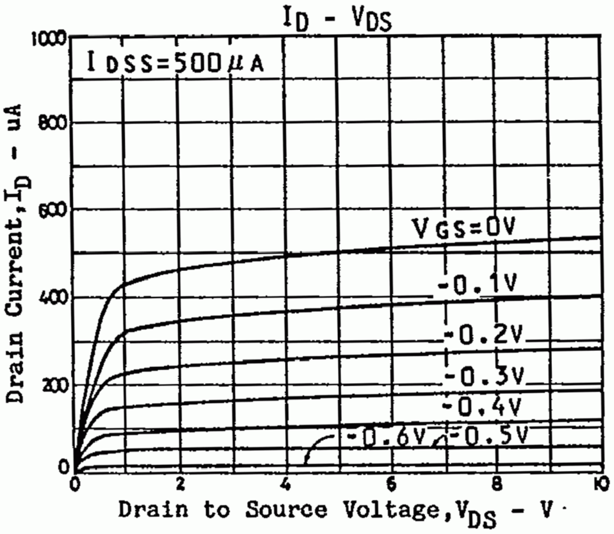
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Gate-Drain breakdown Voltage	BV_{GDO}	I_G= -100μA	-20			V
Gate-Source cut-off Voltage	$V_{GS(off)}$	V_{DS}= 5V, I_D=1μA		-0.6	-1.5	V
Drain Current	I_{DSS}	V_{DS}= 5 V, V_{GS}=0	100		800	μA
Forward Transfer Admittance	$\|Y_{FS}\|$	V_{DS}= 5V, V_{GS}=0, f=1KHz	0.4	1.2		mS
Input Capacitance	C_{iss}	V_{DS}=5V, V_{GS}=0, f=1MHz		3.5		pF
Output Capacitance	C_{RSS}	V_{DS}= 5 V, V_{GS}=0 f = 1MHz		0.65		pF

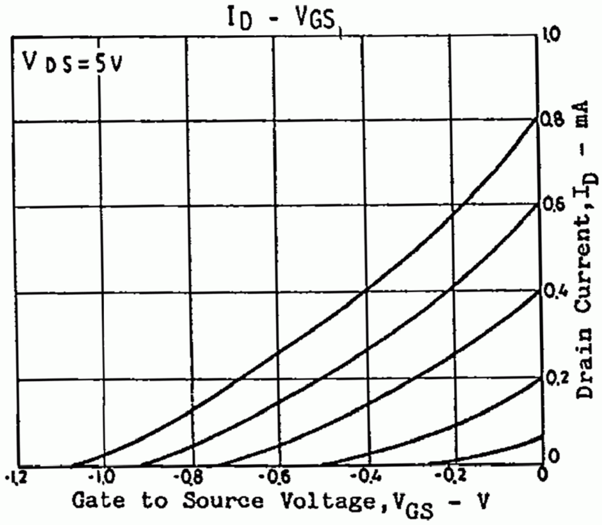
I_{DSS} Classification

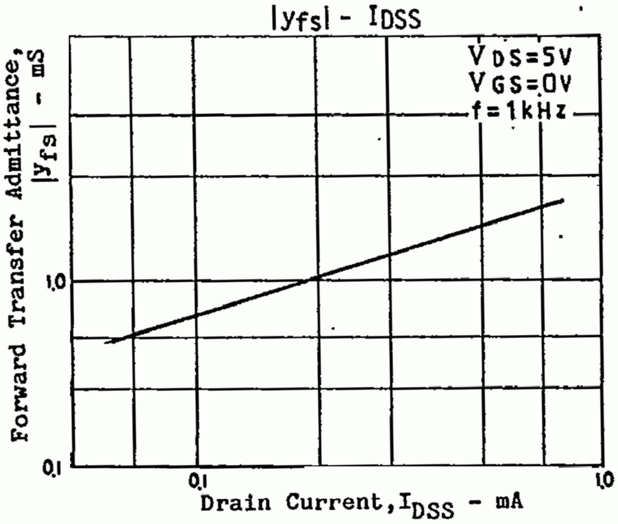
Classification	A	B	C	D	E
I_{DSS} (μA)	100-170	150-240	210-350	320-480	440-800

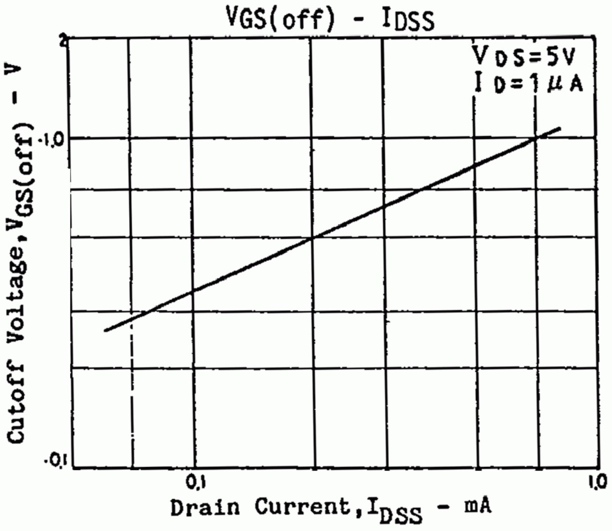
Typical Characteristics

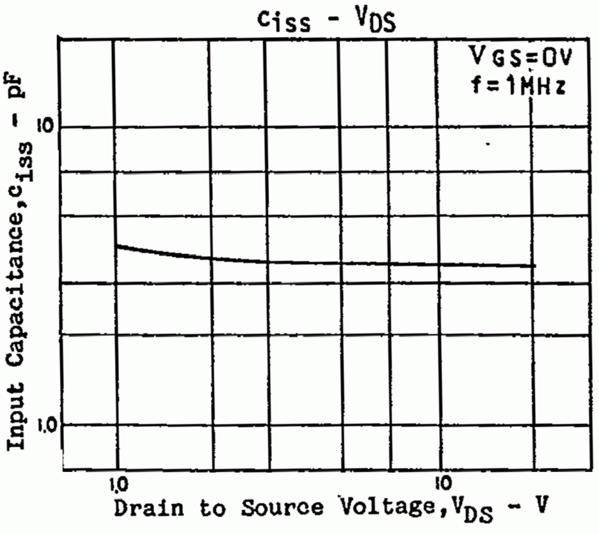




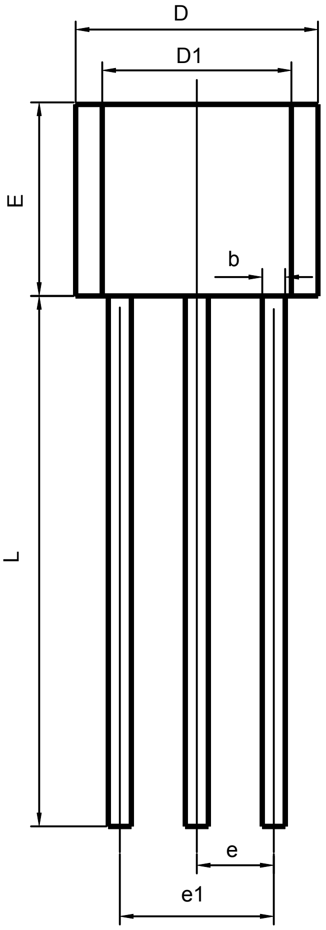


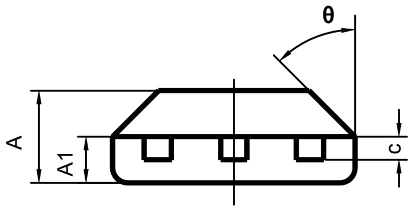






TO-92S PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.240	1.620	0.056	0.064
A1	0.660	0.860	0.026	0.034
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	3.850	4.150	0.152	0.163
D1	2.970	3.270	0.117	0.129
E	3.010	3.310	0.119	0.130
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	15.100	15.500	0.594	0.610
θ	45°TYP		45°TYP	